Philips Semiconductors

Product specification

Dual diode fast, high-voltage

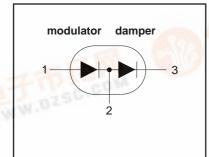
BYM359DX

FEATURES

- Low forward volt drop
- Fast switchingSoft recovery characteristic
- High thermal cycling performance
- Isolated mounting tab

SYMBOL

WWW.DZSC



QUICK REFERENCE DATA

DAMPER MODULATOR		MODULATOR
	V _R =1500 V	V _R =800 V
	V _F ≤ 1.3 V	V _F ≤ 1.45 V
	I _{F(RMS)} =15.7 A	$I_{F(RMS)} = 11 A$
	I _{FSM} ≤ 60 A	I _{FSM} ≤ 60 A
	t _{rr} ≤ 300 ns	t _{rr} ≤ 145 ns

GENERAL DESCRIPTION

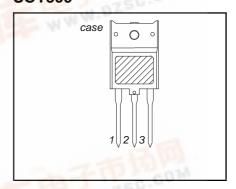
Combined damper and modulator diodes in an isolated plastic envelope for horizontal deflection in colour TV and PC monitors. The BYM359DX contains diodes with performance characteristics designed specifically for applications from 16kHz to 56kHz

The BYM359DX series is supplied in the conventional leaded SOT399 package.

PINNING

PIN	DESCRIPTION
1 modulator anode.	
2	common anode/cathode
3	damper cathode

SOT399



LIMITING VALUES

 $T_i = 25$ °C unless otherwise stated

			DAM	IPER	MODU	LATOR	
SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	MIN	MAX	UNIT
V _{RSM}	Peak non-repetitive reverse voltage.		-	1500	-	800	V
V_{RRM}	Peak repetitive reverse voltage		-	1500	-	600	V
V_{RWM}	Crest working reverse voltage		-	1300	-7.A	600	V
I _{F(AV)} I _{F(RMS)} I _{FRM}	Average forward current RMS forward current Peak repetitive forward current	sinusoidal;a=1.57 t=25 μ s δ = 0.5 T _{hs} \leq 83 °C	華	10 15.7 20	W,OZ	8 11.0 16.0	A A A
I _{FSM}	Peak non-repetitive forward current	t = 10ms t = 8.3 ms sinusoidal; with reapplied V _{RWM(MAX)}	:	60 66	- -	60 66	A A
T _{stg}	Storage temperature Operating junction temperature		-40 -	150 150	-40 -	150 150	Ů,



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ISOLATION LIMITING VALUE & CHARACTERISTIC

T_{hs} = 25 °C unless otherwise specified

115	,					
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65 % ; clean and dustfree	-	-	2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	22	-	pF

THERMAL RESISTANCES

			DAM	PER	MODU	LATOR	
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	with heatsink compound	-	3.5	-	3.5	K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air.	35	-	-	35	K/W

STATIC CHARACTERISTICS

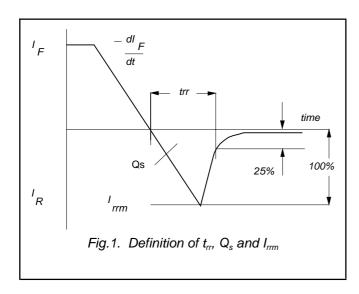
T_i = 25 °C unless otherwise stated

-			DAM	IPER	MODU	LATOR	
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	TYP.	MAX.	UNIT
V _F	Forward voltage Reverse current	$I_F = 6.5 \text{ A}$ $I_F = 6.5 \text{ A}$; $T_j = 125^{\circ}\text{C}$ $V_R = V_{RWM}$	1.1 1.05 10	1.45 1.3 250	1.15 1.1 10	1.55 1.45 100	V V μA
K		$ \begin{vmatrix} V_R = V_{RWM} \\ T_j = 100 \text{ °C} \end{vmatrix} $	50	500	100	600	μA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

			DAM	PER	MODUI	LATOR	
SYMBOL P	PARAMETER	CONDITIONS	TYP.	MAX.	TYP.	MAX.	UNIT
Q _s R	·	$I_F = 1 \text{ A}; V_R \ge 30 \text{ V};$ $-dI_F/dt = 50 \text{ A/}\mu\text{s}$ $2 \text{ A},30 \text{ V},20 \text{ A/}\mu\text{s}$ $I_F = 6.5 \text{ A};$ $dI_E/dt = 50 \text{ A/}\mu\text{s}$	200 1.2 27	300 2.0 -	125 0.5 18.0	145 0.7 -	ns μC V



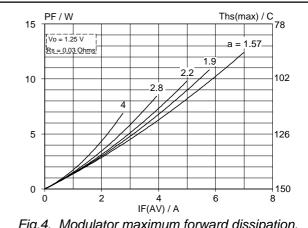
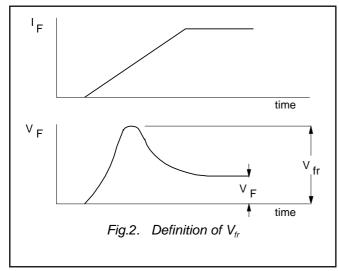


Fig.4. Modulator maximum forward dissipation, $P_F = f(I_{F(AV)})$; sinusoidal current waveform; parameter $a = form \ factor = I_{F(RMS)}/I_{F(AV)}$.



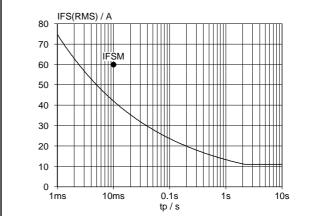


Fig.5. Modulator maximum non-repetitive rms forward current. $I_F = f(t_p)$; sinusoidal current waveform; $T_i = 150$ °C prior to surge with reapplied V_{RWM} .

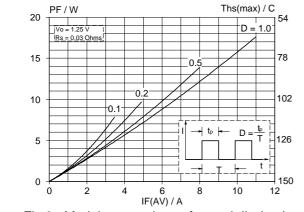


Fig.3. Modulator maximum forward dissipation, $P_F = f(I_{F(AV)})$; square wave current waveform; parameter $D = \text{duty cycle} = t_p/T$.

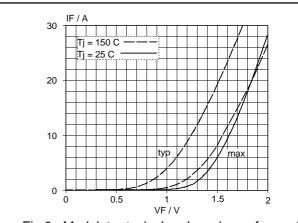
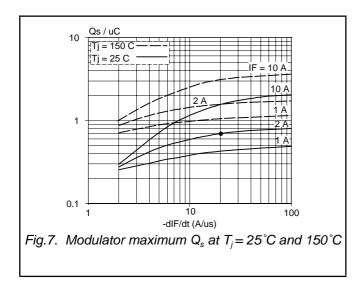


Fig.6. Modulator typical and maximum forward characteristic; $I_F = f(V_F)$; parameter T_i



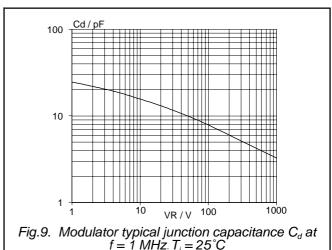


Fig.9. Modulator typical junction capacitance C_d at f=1 MHz, $T_j=25$ °C

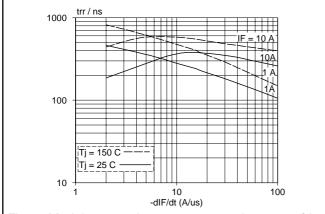


Fig.8. Modulator maximum t_{rr} measured to 25% of I_{rmr} ; $T_j = 25^{\circ}\text{C}$ and 150°C

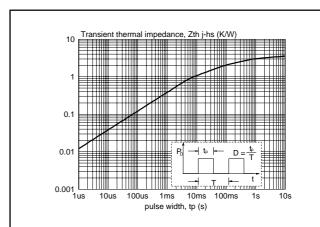


Fig.10. Modulator transient thermal impedance $Z_{th} = f(t_p)$

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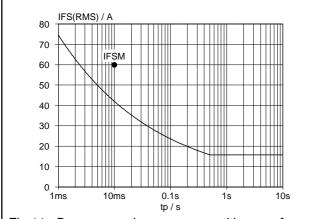


Fig.11. Damper maximum non-repetitive rms forward current. $I_F = f(t_p)$; sinusoidal current waveform; $T_j = 150$ °C prior to surge with reapplied V_{RWM} .

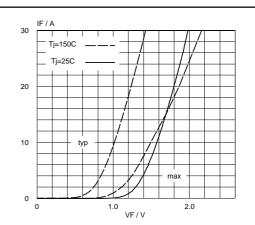


Fig.13. Damper forward characteristic $I_F = f(V_F)$; parameter T_j

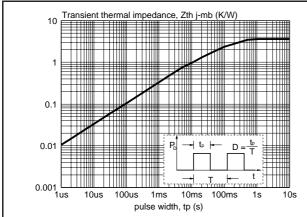
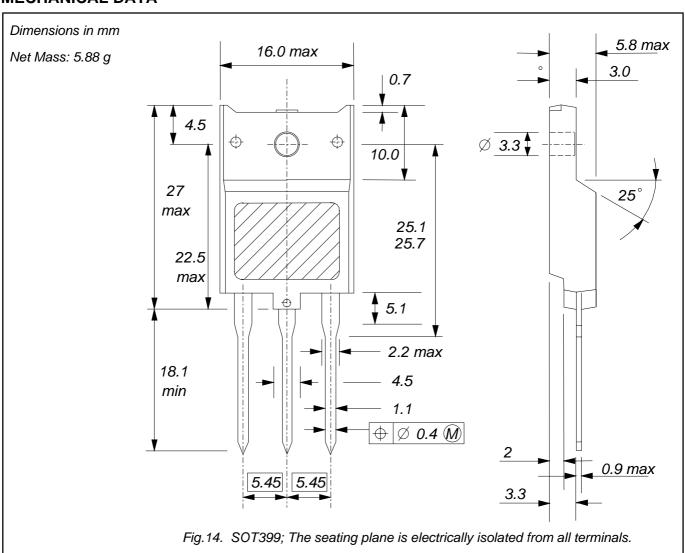


Fig. 12. Damper transient thermal impedance $Z_{th} = f(t_p)$

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MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
Limitim or confessor					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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